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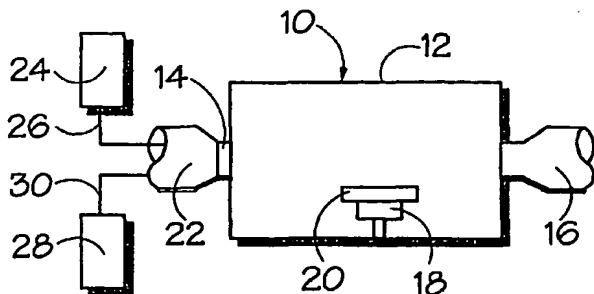
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(54) Title: METHOD AND APPARATUS FOR FORMING EPITAXIAL LAYERS



(57) Abstract: The present invention provides a method of depositing epitaxial layers based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, wherein nitrogen or one of the noble gases is used as a carrier gas, and the invention further provides a Chemical Vapor Deposition apparatus (10) comprising a chamber (12) having a gas input port (14) and a gas output port (16), and means (18) for mounting a silicon substrate within the chamber (12), said apparatus further including a gas source connected to the input port and arranged to provide nitrogen or a noble gas as a carrier gas.

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According to International Patent Classification (IPC) or to both national classification and IPC

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Minimum documentation searched (classification system followed by classification symbols)
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Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, INSPEC

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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☒ Patent family members are listed in annex.

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT		
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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INTERNATIONAL SEARCH REPORT

Information on patent family members

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